

1N914W-AH

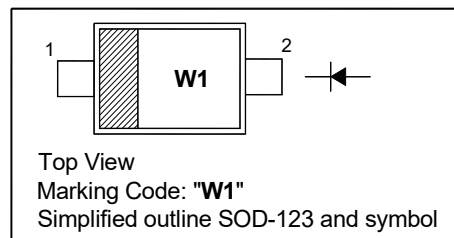
Silicon Epitaxial Planar Switching Diode

Features

- AEC-Q101 Qualified
- Halogen and Antimony Free(HAF), RoHS compliant

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

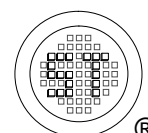


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	215	mA
Non-repetitive Peak Forward Surge Current at $t = 1\text{ s}$ at $t = 1\text{ }\mu\text{s}$	I_{FSM}	1 2	A
Power Dissipation	P_{tot}	400	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	312	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 5\text{ }\mu\text{A}$ at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	75 100	- -	V
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	1	V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	I_R	- - -	25 5 50	nA μA μA
Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	4	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$	t_{rr}	-	4	ns

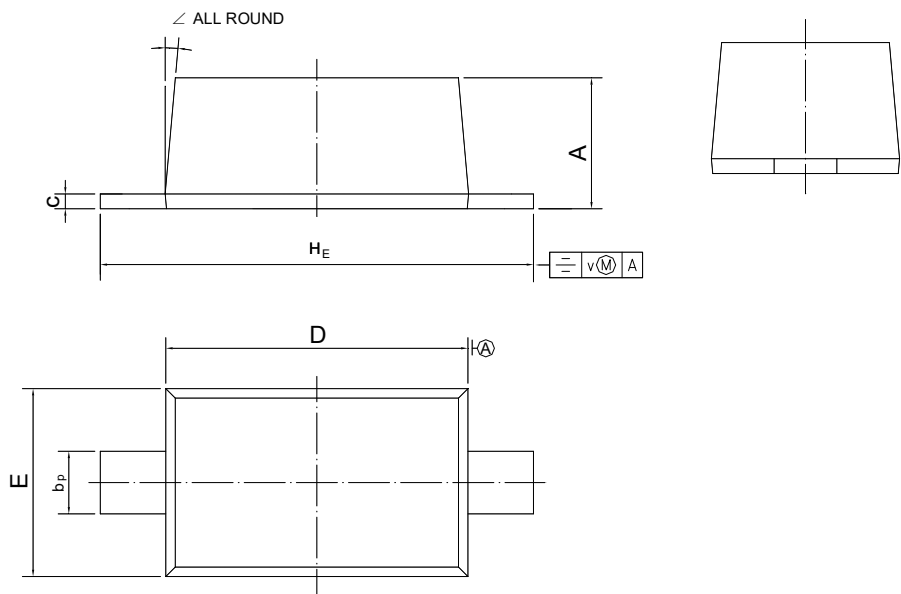


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PACKAGE OUTLINE

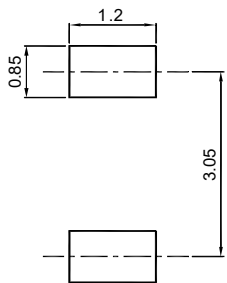
Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	(inch)	mm	(inch)	
SOD-123	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" III " = Cathode line
" W1 " = Part No.
" • " = HAF (Halogen and Antimony Free)
Font type: Arial

